

# HVM131S

## Silicon Epitaxial Planar Pin Diode for Antenna Switching

# HITACHI

Rev. 1  
Oct. 1995

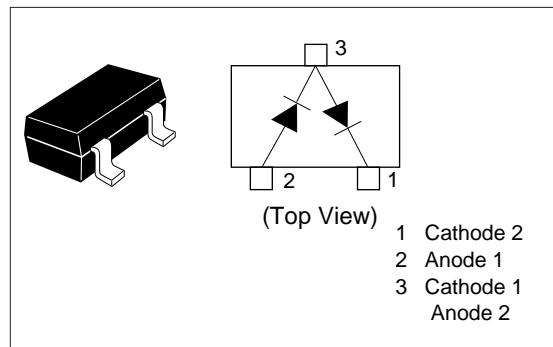
### Features

- Low capacitance.(C=0.8pF max)
- Low forward resistance. ( $r_f=1.0\Omega$  max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

### Ordering Information

Type No.	Laser Mark	Package Code
HVM131S	P5	MPAK

### Outline



### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V <sub>RM</sub>	65	V
Reverse voltage	V <sub>R</sub>	60	V
Forward current	I <sub>F</sub> *	100	mA
Power dissipation	P <sub>d</sub> *	150	mW
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

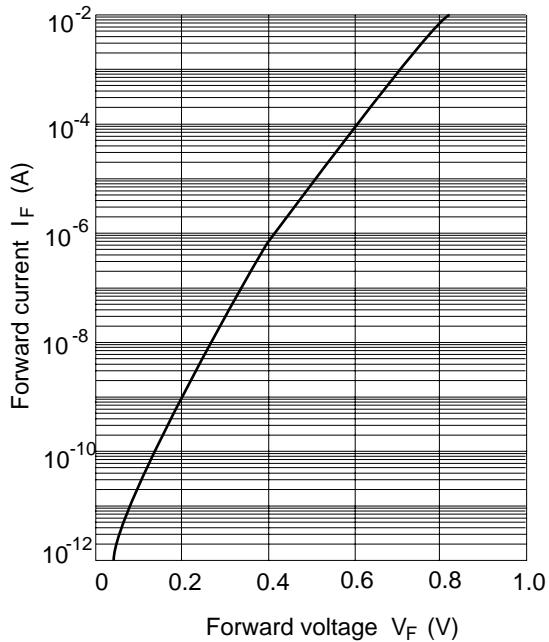
\* Two device total

### Electrical Characteristics (Ta = 25°C) \*

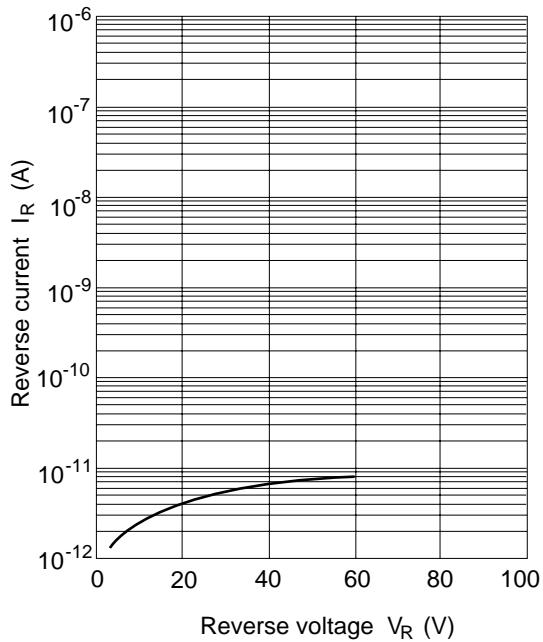
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V <sub>F</sub>	—	—	1.0	V	I <sub>F</sub> = 10 mA
Reverse current	I <sub>R</sub>	—	—	0.1	µA	V <sub>R</sub> = 60 V
Capacitance	C	—	—	0.8	pF	V <sub>R</sub> = 1 V , f = 1 MHz
Forward resistance	r <sub>f</sub>	—	—	1.0	Ω	I <sub>F</sub> = 10 mA, f = 100 MHz

\* Per one device

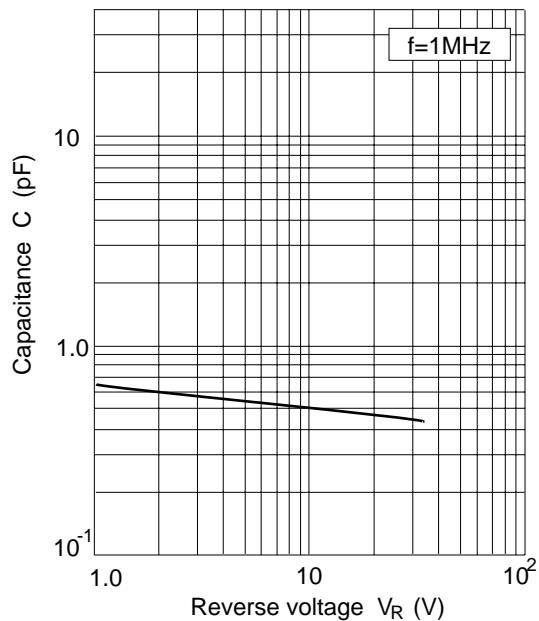
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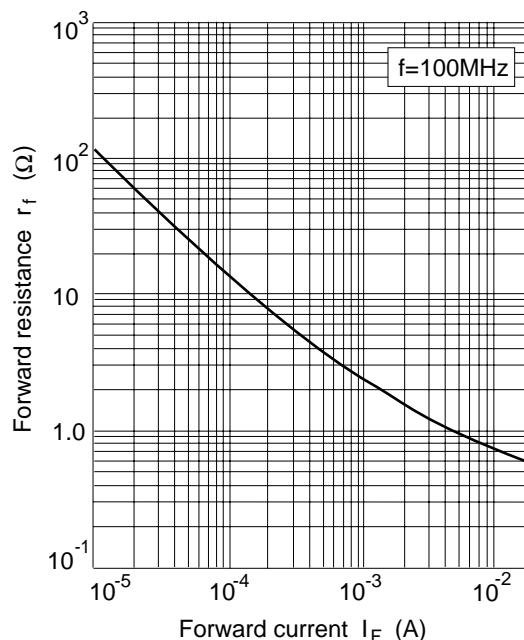
**Fig.1** Forward current Vs.  
Forward voltage



**Fig.2** Reverse current Vs.  
Reverse voltage



**Fig.3** Capacitance Vs.  
Reverse voltage



**Fig.4** Forward resistance Vs.  
Forward current

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## Package Dimensions

Unit: mm

